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	1	TALWAT et al., "Study of Thermal Processing (LTP) to Meet Sub 130 nm Node Shallow Junction Requirements", 2002, pages 175-177	<input checked="" type="checkbox"/>
	2	ITO et al., "Flash Lamp Annealing Technology for Ultra-shallow Junction Formation", Extended Abstracts of International Workshop on Junction Technology, 2002, pages 23-26	<input checked="" type="checkbox"/>
	3	KAGAWA et al., "Influence of pulse duration on KrF excimer laser annealing process for ultra shallow junction formation", Extended Abstracts of International Workshop on Junction Technology, 2002, pages 31-34	<input checked="" type="checkbox"/>
	4	Yamamoto et al., "Impact of Pre-Amorphization for the Reduction of Contact Resistance Using Laser Thermal Process, Extended Abstracts of International Workshop on Junction Technology, 2002, pages 27-30	<input checked="" type="checkbox"/>
	5	ITO et al., "Improvement of Threshold Voltage Roll-off by Ultra-shallow Junction Formed by Flash Lamp Annealing", Symposium on VLSI Technology Digest of Technical Papers, 2003	<input checked="" type="checkbox"/>

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